



20V P-Channel MOSFET



SOP-8

Pin Definition:

- 1. Source
- 2. Source
- 3. Source
- 4. Gate
- 5, 6, 7, 8. Drain

PRODUCT SUMMARY

V _{DS} (V)	$R_{DS(on)}(m\Omega)$	I _D (A)
-20	45 @ V _{GS} = -4.5V	-5.4
	70 @ V _{GS} = -2.5V	-4.2

Features

- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

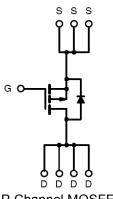
Application

- Load Switch
- PA Switch

Ordering Information

Part No.	No. Package Packii	
TSM9433CS RL	SOP-8	2.5Kpcs / 13" Reel

Block Diagram



P-Channel MOSFET

Absolute Maximum Rating (Ta = 25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V_{DS}	-20	V	
Gate-Source Voltage		V_{GS}	±12	V	
Continuous Drain Current		I _D	-5.4	Α	
Pulsed Drain Current		I _{DM}	-20	Α	
Continuous Source Current (Diode Co	onduction) ^{a,b}	I _S	-2.6	Α	
Maximum Power Dissipation	Ta = 25°C	- P _D	2.5	W	
	Ta = 70°C		1.6		
Operating Junction Temperature		T_J	+150	°C	
Operating Junction and Storage Temperature Range		T _J , T _{STG}	- 55 to +150	°C	

Thermal Performance

Parameter	Symbol	Limit	Unit
Junction to Case Thermal Resistance	R⊖ _{JC}	30	°C/W
Junction to Ambient Thermal Resistance (PCB mounted)	RO _{JA}	50	°C/W

1/6

Notes:

- a. Pulse width limited by the Maximum junction temperature
- b. Surface Mounted on FR4 Board, t ≤ 5 sec.

Version: A07



TSM9433

20V P-Channel MOSFET

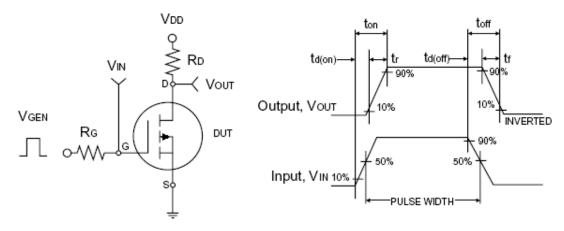


Electrical Specifications (Ta = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = -250uA$	BV _{DSS}	-20			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	$V_{GS(TH)}$	-0.6		-1.4	V
Gate Body Leakage	$V_{GS} = \pm 12V, V_{DS} = 0V$	I _{GSS}	-		±100	nA
Zero Gate Voltage Drain Current	$V_{DS} = -20V, V_{GS} = 0V$	I _{DSS}			-1.0	μA
On-State Drain Current ^a	$V_{DS} = -5V, V_{GS} = -4.5V$	I _{D(ON)}	-15			Α
	$V_{GS} = -4.5V$, $I_D = -5.4A$, ,		32	55	mΩ
Drain-Source On-State Resistance ^a	$V_{GS} = -2.5V$, $I_D = -4.2A$	$R_{DS(ON)}$		52	75	
Forward Transconductance ^a	$V_{DS} = -9V, I_{D} = -5.1A$	g _{fs}		11		S
Diode Forward Voltage	$I_S = -1.7A$, $V_{GS} = 0V$	V_{SD}		-0.8	-1.2	V
Dynamic ^b		_				
Total Gate Charge	\/ - 10\/ - 5.40	Q_g		6	9	
Gate-Source Charge	$V_{DS} = -10V, I_{D} = -5.4A,$ $V_{GS} = -4.5V$	Q_gs	-	1.4		nC
Gate-Drain Charge		Q_{gd}	-	1.9		
Input Capacitance	\/ - 40\/ \/ - 0\/	C_{iss}	-	640		
Output Capacitance	$V_{DS} = -10V, V_{GS} = 0V,$ f = 1.0MHz	C _{oss}	1	180		pF
Reverse Transfer Capacitance		C_{rss}		90		
Switching ^c						
Turn-On Delay Time	V_{DD} = -10V, R_L = 10Ω, I_D = -1A, V_{GEN} = -4.5V, R_G = 6Ω	$t_{d(on)}$		22	35	
Turn-On Rise Time		t _r		35	55	200
Turn-Off Delay Time		t _{d(off)}		45	70	nS
Turn-Off Fall Time		t _f		25	50	

Notes:

- a. pulse test: PW $\leq 300 \mu S$, duty cycle $\leq 2\%$ b. For DESIGN AID ONLY, not subject to production testing.
- b. Switching time is essentially independent of operating temperature.



Switching Test Circuit

Switchin Waveforms

2/6 Version: A07

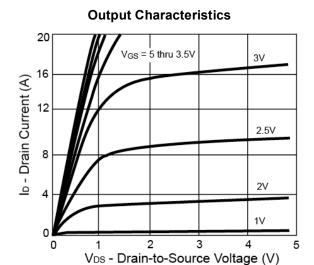




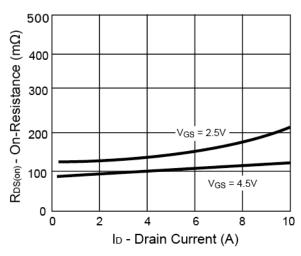




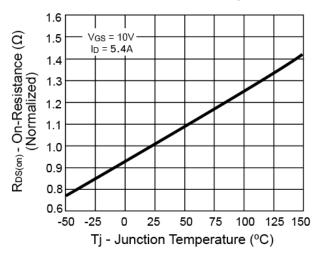
Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)



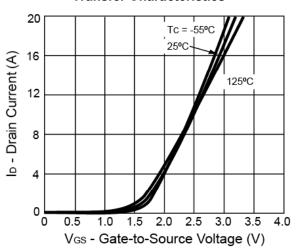
On-Resistance vs. Drain Current



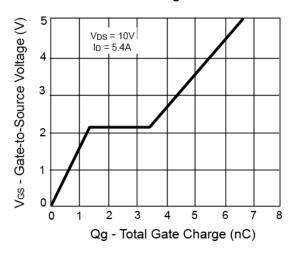
On-Resistance vs. Junction Temperature



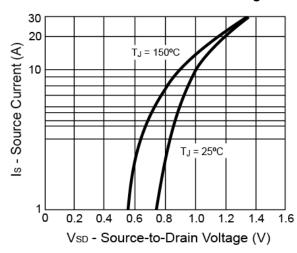
Transfer Characteristics



Gate Charge



Source-Drain Diode Forward Voltage



3/6 Version: A07



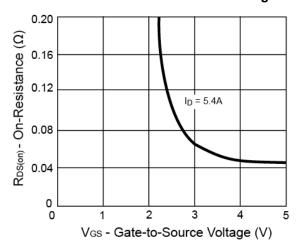


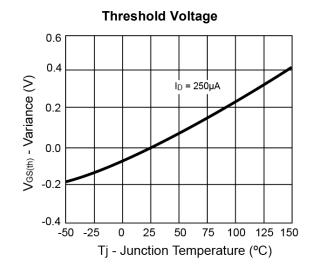




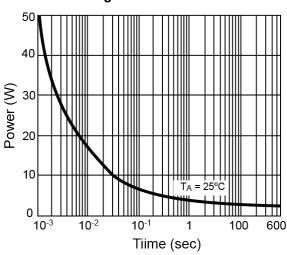
Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)

On-Resistance vs. Gate-Source Voltage

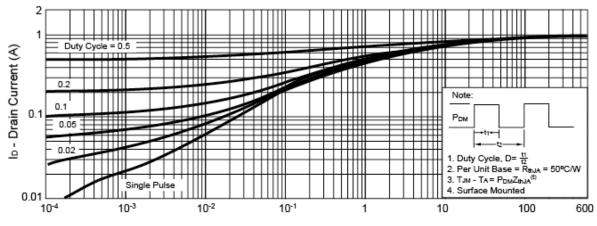




Single Pulse Power



Normalized Thermal Transient Impedance, Junction-to-Ambient



Square Wave Pulse Duration (sec)

4/6 Version: A07

INCHES

0.05BSC

MAX.

0.196

0.157

0.068

0.019

0.009

7°

0.244

0.019

0.049

MIN

0.189

0.150

0.054

0.014

0.016

0.004

0°

0.229

0.010



SOP-8 DIMENSION

MAX

5.00

4.00

1.75

0.49

1.25

0.25

7°

6.20

0.50

MILLIMETERS

1.27BSC

MIN

4.80

3.80

1.35

0.35

0.40

0.10

0°

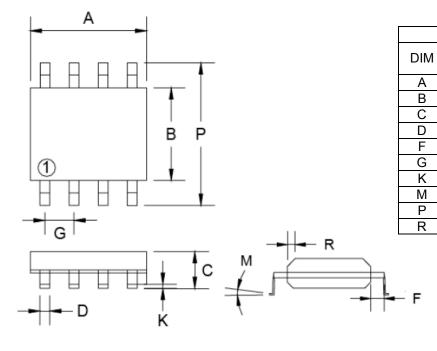
5.80

0.25

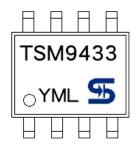




SOP-8 Mechanical Drawing



Marking Diagram



Y = Year Code

M = Month Code

(A=Jan, B=Feb, C=Mar, D=Apl, E=May, F=Jun, G=Jul, H=Aug,

I=Sep, J=Oct, K=Nov, L=Dec)

L = Lot Code

5/6 Version: A07



TSM9433 20V P-Channel MOSFET

Notice

Specifications of the products displayed herein are subject to change without notice. TSC or anyone on its behalf, assumes no responsibility or liability for any errors or inaccuracies.

Information contained herein is intended to provide a product description only. No license, express or implied, to any intellectual property rights is granted by this document. Except as provided in TSC's terms and conditions of sale for such products, TSC assumes no liability whatsoever, and disclaims any express or implied warranty, relating to sale and/or use of TSC products including liability or warranties relating to fitness for a particular purpose, merchantability, or infringement of any patent, copyright, or other intellectual property right.

The products shown herein are not designed for use in medical, life-saving, or life-sustaining applications. Customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify TSC for any damages resulting from such improper use or sale.

6/6 Version: A07